## Transistors

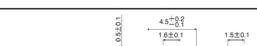
# Small switching (30V, 2A) 25K2103

#### Features

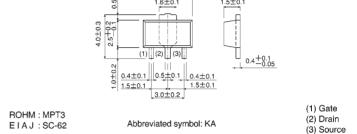
- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Wide SOA (safe operating area).
- 4) Low-voltage drive (4V).
- 5) Easily designed drive circuits.
- 6) Easy to use in parallel.

#### Structure

Silicon N-channel MOSFET



External dimensions (Units: mm)



#### •Absolute maximum ratings (Ta = $25^{\circ}$ C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		VDSS	30	V
Gate-source voltage		Vgss	±20	V
Droin ourront	Continuous	lo	2	А
Drain current	Pulsed	lde*1	8	А
Reverse drain	Continuous	lor	2	А
current	Pulsed	IDRP <sup>*1</sup>	8	А
Total power dissipation		Po	0.5 2* <sup>2</sup>	W
Channel temperature		Tch	150	Ĉ
Storage temperature		Tstg	-55~+150	°C

\*1 Pw $\leq$ 10  $\mu$ s, Duty cycle $\leq$ 1% \*2 When mounted on a 40  $\times$  40  $\times$  0.7 mm alumina board.

#### Packaging specifications

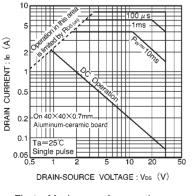
	Package	Taping
Туре	Code	T100
	Basic ordering unit (pieces)	1000
2SK2103		0

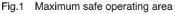
#### Electrical characteristics (Ta = 25°C)

			_			
Parameter	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Gate-source leakage	I <sub>GSS</sub>	-	-	±100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)}_{\text{DSS}}$	30	_	_	V	ID=1mA, VGS=0V
Zero gate voltage drain current	loss	-	-	10	μA	VDS=30V, VGS=0V
Gate threshold voltage	VGS (th)	1.0	_	2.5	V	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA
Static drain-source on-state		_	0.25	0.4	Ω	ID=1A, VGS=10V
resistance	RDS (on)	_	0.38	0.6		ID=1A, VGS=4V
Forward transfer admittance	Y <sub>fs</sub>  *	1.0	_	-	S	ID=1A, VDS=10V
Input capacitance	Ciss	_	230	-	pF	V <sub>DS</sub> =10V
Output capacitance	Coss	_	120	_	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	Crss	-	60	-	pF	f=1MHz
Turn-on delay time	td (on)	-	10	-	ns	I□=1A, V□□≑15V
Rise time	tr	-	25	-	ns	V <sub>GS</sub> =10V
Turn-off delay time	td (off)	_	60	_	ns	RL=15Ω
Fall time	tr	_	60	-	ns	Rg=10Ω
Reverse recovery time	trr	_	70	-	ns	IDR=2A, VGS=0V, di/dt=50A/ $\mu$ s

\* Pw≦300 μs, Duty cycle≦1%

#### Electrical characteristic curves





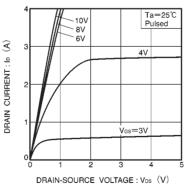
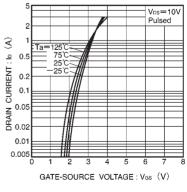
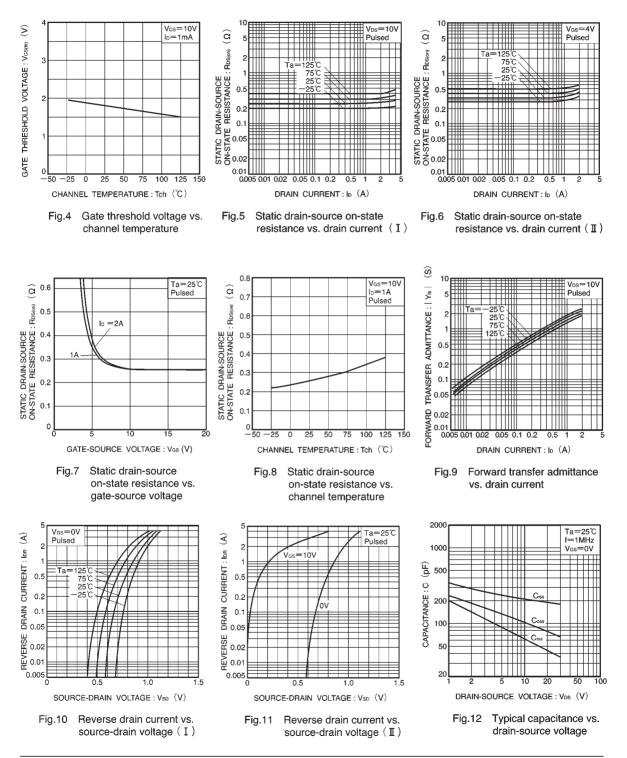


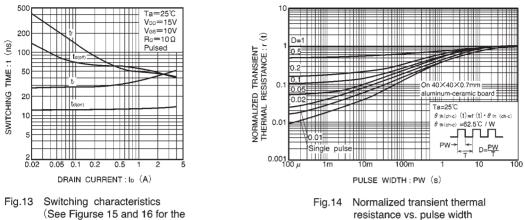
Fig.2 Typical output characteristics





## Transistors





- (See Figurse 15 and 16 for the measurement circuit and resultant waveforms)
- Switching characteristics measurement circuit

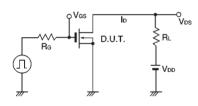


Fig.15 Switching time measurement circuit

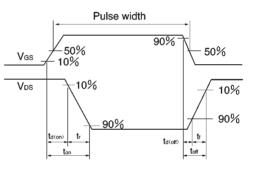


Fig.16 Switching time waveforms

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